

# Thermal Casimir-Polder force between an atom and a dielectric plate: thermodynamics and experiment

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## Abstract

The low-temperature behavior of the Casimir-Polder free energy and entropy for an atom near a dielectric plate are found on the basis of the standard Lifshitz theory and its generalization including the effects of spatial dispersion (L. P. Pitaevskii, arXiv:0801.0656). The Lifshitz theory with neglect of the dc conductivity of the plate material is shown to be thermodynamically consistent. With inclusion of dc conductivity, both the Lifshitz theory (for all dielectrics) and its generalization (for a wide range of dielectrics) violate the Nernst heat theorem. The proposed generalization is also inconsistent with measurement data at a 70% confidence level.

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Recently, considerable interest has been focused on the interaction of atoms with metal and dielectric plates (walls) at separation distances  $a$  from about 100 nm to a few micrometers where the retardation effects of the electromagnetic field play an important role. The relativistic description of the fluctuating interaction of atoms with an ideal metal plate at zero temperature was pioneered by Casimir and Polder [1] who obtained the interaction energy in the form  $E(a) = -3\hbar c\alpha_0/(8\pi a^4)$ , where  $\alpha_0 \equiv \alpha(0)$  is the static atomic polarizability,  $\hbar$  and  $c$  are the Planck constant and the velocity of light. Lifshitz [2] developed the general theory of dispersion forces between two dielectric semispaces at a temperature  $T$  in thermal equilibrium with plane parallel boundary surfaces separated by a gap  $a$  of arbitrary width much larger than interatomic distances. This theory describes material properties with a dielectric permittivity that depends only on frequency. It includes both nonrelativistic (when  $a \ll \lambda_0$  where  $\lambda_0$  is the characteristic absorption wavelength of the semispace material) and relativistic (when  $a \gg \lambda_0$ ) limiting cases. If the material of one of the plates is rarefied, the general formula for the energy of the atom-wall interaction is obtained. For an ideal metal plate at  $T = 0$  it leads to the Casimir-Polder result. In the high temperature (large separation) limit the interaction free energy of an atom with an ideal metal plate is given by  $\mathcal{F}(a, T) = -k_B T\alpha_0/(4a^3)$ , where  $k_B$  is the Boltzmann constant. For a dielectric plate with the static dielectric permittivity  $\varepsilon_0 \equiv \varepsilon(0)$ , the free energy acquires an additional factor  $r_0 = (\varepsilon_0 - 1)/(\varepsilon_0 + 1)$  which goes to unity when  $\varepsilon_0 \rightarrow \infty$ .

In the last few years the Casimir-Polder and Lifshitz formulas have been used for the interpretation of many experiments on quantum reflection and Bose-Einstein condensation of ultra-cold atoms near a variety of surfaces (see, e.g., [3, 4, 5, 6, 7, 8, 9, 10] and references therein). The Lifshitz theory was also extensively applied for the interpretation of measurements of the Casimir force between two macrobodies made of metals and semiconductors (see, e.g., [11, 12, 13, 14, 15, 16, 17, 18]). All these experiments have attracted widespread attention from diverse fields ranging from condensed matter physics and nanotechnology to atomic physics, elementary particle physics, gravitation and cosmology. However, the application of the Lifshitz theory to the real material bodies used in experiments has resulted in a puzzle. It was found that for metallic test bodies with perfect crystal lattices the calculational results are in contradiction with thermodynamics [19, 20] and experimental data [12, 13, 14] if the relaxation processes of conduction electrons are included into the model of the dielectric response used in the Lifshitz theory. For semiconductor and dielectric

materials whose conductivity goes to zero with vanishing temperature, the calculational results using the Lifshitz theory were also shown to be in contradiction with thermodynamics [21, 22] and experiment [17, 23] when the dc conductivity of a dielectric or a high-resistivity semiconductor plate is included.

An interesting attempt to find the physical explanation for some of these puzzling results is undertaken in Ref. [24]. It takes into account the Debye screening of the electrostatic field by free charge carriers in the conductor. The effect of screening of the electric field in conductors of finite size on the thermal Casimir force was first discussed in Ref. [25]. In Ref. [26] a detailed demonstration was given that this screening prevents the use of the Drude-like dielectric permittivities for the description of the thermal Casimir force between metallic plates of finite size. Reference [24] provides a generalized high-temperature asymptotic expression for the Lifshitz free energy of atom-plate interaction in the presence of spatial dispersion. This effectively results in a modified reflection coefficient for the transverse magnetic (TM) mode at zero frequency in comparison to the Lifshitz theory (as noted in Ref. [24], the above mentioned puzzles arise only in the zero-frequency term of the Lifshitz formula). The reflection coefficient for the transverse electric (TE) mode at zero frequency for dielectric materials is equal to zero regardless of the dc conductivity. Reference [24] arrives at expressions for the atom-plate free energy and force depending on the total density  $n$  of charge carriers (electrons and holes) and applies them to the case of the fused silica used in the experiment [10]. At fixed  $T$  a continuous crossover between the cases of an insulator with  $\varepsilon_0 < \infty$  and a good metal is investigated depending on the value of  $n$ .

Here, we find the low-temperature behavior of the entropy of the Casimir-Polder atom-plate interaction both in the framework of the commonly accepted Lifshitz theory and its generalization, as proposed in Ref. [24]. We demonstrate that if the dc conductivity of dielectrics is disregarded (in this case the generalization [24] with  $n = 0$  reduces to the standard Lifshitz theory) the Casimir-Polder entropy goes to zero when the temperature vanishes, i.e., the Nernst heat theorem is satisfied. If the dc conductivity is included, the standard Lifshitz theory violates Nernst's theorem. The generalization [24] is in agreement with Nernst's theorem for dielectrics whose charge carrier density vanishes when  $T$  goes to zero. However, for dielectrics whose charge carrier density is temperature-independent (for such materials conductivity goes to zero with  $T$  not due to the vanishing  $n$  but due to the vanishing mobility of the charge carriers) the generalization of the Lifshitz theory,

as proposed in Ref. [24], is shown to violate the Nernst theorem. It should be noted that fused silica, to which the suggested generalization is applied [24], belongs to this latter class of materials. Finally we demonstrate that the suggested generalization of TM reflection coefficient at zero frequency is inconsistent with the measurement data of the difference Casimir force between a metal sphere and a semiconductor plate [17].

We start with the standard Lifshitz formula for the free energy of an atom-plate interaction [2, 5, 6]

$$\mathcal{F}(a, T) = \frac{k_B T}{8a^3} \sum_{l=0}^{\infty} \prime \Phi_A(\zeta_l), \quad (1)$$

where  $\zeta_l = \xi_l/\omega_c$ ,  $\xi_l = 2\pi k_B T l/\hbar$  are the Matsubara frequencies,  $\omega_c = c/(2a)$ , prime indicates that the  $l = 0$  term has to be multiplied by  $1/2$ , and

$$\begin{aligned} \Phi_A(x) = & -\alpha(i\omega_c x) \int_x^{\infty} dy e^{-y} \{2y^2 r_{\text{TM}}(ix, y) \\ & -x^2 [r_{\text{TM}}(ix, y) + r_{\text{TE}}(ix, y)]\}. \end{aligned} \quad (2)$$

The reflection coefficients are defined through the frequency-dependent permittivity  $\varepsilon_l = \varepsilon(i\omega_c \zeta_l)$

$$\begin{aligned} r_{\text{TM}}(ix, y) &= \frac{\varepsilon_l y - \sqrt{y^2 + x^2(\varepsilon_l - 1)}}{\varepsilon_l y + \sqrt{y^2 + x^2(\varepsilon_l - 1)}}, \\ r_{\text{TE}}(ix, y) &= \frac{y - \sqrt{y^2 + x^2(\varepsilon_l - 1)}}{y + \sqrt{y^2 + x^2(\varepsilon_l - 1)}}. \end{aligned} \quad (3)$$

The atomic dynamic polarizability can be represented with sufficient precision using the single oscillator model [5]

$$\alpha(i\omega_c \zeta_l) = \frac{\alpha_0}{1 + \beta_A^2 \zeta_l^2} \quad (4)$$

with a dimensionless constant  $\beta_A$ .

Using the Abel-Plana formula [27], the free energy (1) can be equivalently represented in the form

$$\mathcal{F}(a, T) = E(a) + i \frac{k_B T}{8a^3} \int_0^{\infty} dt \frac{\Phi_A(i\tau t) - \Phi_A(-i\tau t)}{e^{2\pi t} - 1}, \quad (5)$$

where  $E(a)$  is the Casimir-Polder energy at zero temperature,  $\tau = 2\pi T/T_{\text{eff}}$  and the effective temperature is defined from  $k_B T_{\text{eff}} = \hbar\omega_c$ .

We are interested in the primary contribution to the low-temperature asymptotic behavior of the Casimir-Polder free energy (1) in the case  $\varepsilon_0 < \infty$  (i.e., with dc conductivity disregarded). For this purpose, as shown in [21, 22], it is sufficient to restrict ourselves to a

frequency-independent permittivity  $\varepsilon_l = \varepsilon_0$ . By expanding  $\Phi_A(x)$  in Eq. (2) in powers of  $x$  and using of Eqs. (3) and (4), one obtains

$$\Phi_A(x) = -\alpha_0 \left[ 4r_0 + r_0 \left( 4\beta_A^2 - 2\frac{\varepsilon_0}{\varepsilon_0 + 1} - 1 \right) x^2 + C_D(\varepsilon_0)x^3 \right], \quad (6)$$

where the terms in higher powers are omitted and the following notation is introduced

$$C_D(\varepsilon_0) = r_0 \frac{7\varepsilon_0 + 1}{3(\varepsilon_0 + 1)} + \frac{(\sqrt{\varepsilon_0} - 1) [(3\varepsilon_0^2 + 1)(2\sqrt{\varepsilon_0} + 1) + 3\varepsilon_0(\sqrt{\varepsilon_0} - 1)]}{3(\sqrt{\varepsilon_0} + 1)(\varepsilon_0 + 1)^2} \\ + \frac{2\varepsilon_0^2}{(\varepsilon_0 + 1)^{5/2}} \left( \text{Artanh} \sqrt{\frac{\varepsilon_0}{\varepsilon_0 + 1}} - \text{Arcoth} \sqrt{\varepsilon_0 + 1} \right). \quad (7)$$

In the limiting case  $\varepsilon_0 \rightarrow 1$  we have  $C_D(\varepsilon_0) \rightarrow 0$  as expected. The typical values of this coefficient are  $C_D(\varepsilon_0) = 0.585$  and  $7.60$  for  $\varepsilon_0 = 1.5$  and  $16$ , respectively. For the commonly used dielectrics such as  $\text{SiO}_2$  with  $\varepsilon_0 = 3.81$  and  $\text{Si}$  with  $\varepsilon_0 = 11.67$ , from Eq. (7) we get  $C_D(\varepsilon_0) = 2.70$  and  $6.33$ , respectively.

As a result, from Eq. (6) we obtain

$$\Phi_A(i\tau t) - \Phi_A(-i\tau t) = 2\tau^3 t^3 \alpha_0 C_D(\varepsilon_0). \quad (8)$$

Then from Eq. (5) the Casimir-Polder free energy is given by

$$\mathcal{F}(a, T) = E(a) - \frac{\hbar c \pi^3}{240 a^4} \alpha_0 C_D(\varepsilon_0) \left( \frac{T}{T_{\text{eff}}} \right)^4 \quad (9)$$

and the Casimir-Polder entropy by

$$S(a, T) = -\frac{\partial \mathcal{F}(a, T)}{\partial T} = \frac{\pi^3 k_B}{30 a^3} \alpha_0 C_D(\varepsilon_0) \left( \frac{T}{T_{\text{eff}}} \right)^3. \quad (10)$$

As can be seen from Eq. (10), the entropy goes to zero when  $T$  vanishes in accordance with the Nernst heat theorem. Thus, the Lifshitz theory of the atom-plate interaction is thermodynamically consistent if the dc conductivity of dielectric plate is disregarded.

In electrodynamics the inclusion of the dc conductivity is equivalent to the replacement of  $\varepsilon(\omega)$  with

$$\tilde{\varepsilon}(\omega) = \varepsilon(\omega) + \frac{4\pi i \sigma_0(T)}{\omega}. \quad (11)$$

In the Lifshitz theory this leads to only negligible additions to all the terms at  $\omega = i\xi_l$  with  $l \geq 1$  in the free energy and entropy. These additions exponentially decay to zero with vanishing temperature [21, 22]. However, the term with  $l = 0$  is modified because according

to Eq. (3)  $r_{\text{TM}}(0, y) = r_0$  is replaced with  $\tilde{r}_{\text{TM}}(0, y) = 1$ . As a result, with dc conductivity included the free energy of the atom-plate interaction at low temperature is given by

$$\tilde{\mathcal{F}}(a, T) = \mathcal{F}(a, T) - \frac{k_B T}{4a^3}(1 - r_0)\alpha_0, \quad (12)$$

where  $\mathcal{F}(a, T)$  is defined in Eq. (9). From (12) one immediately arrives at the violation of the Nernst heat theorem

$$\tilde{S}(a, 0) = \frac{k_B \alpha_0}{4a^3}(1 - r_0) > 0. \quad (13)$$

Now we apply the above thermodynamic test to the generalization of the Lifshitz theory, as proposed in Ref. [24]. In this case, the reflection coefficient  $r_{\text{TM}}(0, y)$ , as given in Eq. (3) (the standard Lifshitz theory), is modified to

$$r_{\text{TM}}^{\text{mod}}(0, y) = \frac{\varepsilon_0 \sqrt{4a^2 \kappa^2 + y^2} - y}{\varepsilon_0 \sqrt{4a^2 \kappa^2 + y^2} + y}, \quad (14)$$

where  $\kappa^2 = 4\pi e^2 n / (\varepsilon_0 k_B T)$ , while all the coefficients  $r_{\text{TM,TE}}(i\zeta_l, y)$  with  $l \geq 1$  and also  $r_{\text{TE}}(0, y) = 0$  remain unchanged (note that  $\kappa$  is connected with the so-called *Debye radius*,  $\kappa = 1/R_D$ ). When the total density of charge carriers  $n$  is zero, Eq. (14) leads to the same result as (3). For  $n \rightarrow \infty$ , at fixed  $T \neq 0$ ,  $r_{\text{TM}}^{\text{mod}}(0, y) = 1$ , as in the case of the standard Lifshitz theory when the dc conductivity is included.

The calculation of the free energy at low temperature with the modified reflection coefficient (14) results in

$$\begin{aligned} \mathcal{F}^{\text{mod}}(a, T) &= \mathcal{F}(a, T) - \frac{k_B T \alpha_0}{8a^3} \int_0^\infty r_{\text{TM}}^{\text{mod}}(0, y) e^{-y} y^2 dy \\ &\quad + \frac{k_B T \alpha_0}{4a^3} r_0, \end{aligned} \quad (15)$$

where  $\mathcal{F}(a, T)$  is defined in (9). The respective Casimir-Polder entropy is given by

$$\begin{aligned} S^{\text{mod}}(a, T) &= S(a, T) + \frac{k_B \alpha_0}{4a^3} \left[ \frac{1}{2} \int_0^\infty r_{\text{TM}}^{\text{mod}}(0, y) e^{-y} y^2 dy - r_0 \right] \\ &\quad + \frac{k_B T \alpha_0}{8a^3} \int_0^\infty \frac{\partial r_{\text{TM}}^{\text{mod}}(0, y)}{\partial T} e^{-y} y^2 dy, \end{aligned} \quad (16)$$

with  $S(a, T)$  defined in Eq. (10). It is easily seen that the last term on the right-hand side of Eq. (16) goes to zero when temperature vanishes, regardless of the temperature dependence of  $n$ . The second term on the right-hand side of Eq. (16) is more involved. If  $n(T)$  exponentially decays to zero with temperature (as is true for insulators and intrinsic

semiconductors), then so does  $\kappa(T)$ . As a result,  $r_{\text{TM}}^{\text{mod}}(0, y) \rightarrow r_0$  and the entropy  $S^{\text{mod}}(a, 0)$  is equal to zero, in accordance with the Nernst theorem. However, if  $n$  does not go to zero when  $T$  goes to zero (this is true, for instance, for dielectric materials, such as semiconductors doped below critical and solids with ionic conductivity),  $\kappa \rightarrow \infty$  with vanishing temperature and  $r_{\text{TM}}^{\text{mod}}(0, y) \rightarrow 1$  when  $T \rightarrow 0$ . In this case we obtain from Eq. (16)

$$S^{\text{mod}}(a, 0) = \tilde{S}(a, 0) = \frac{k_B \alpha_0}{4a^3} (1 - r_0) > 0, \quad (17)$$

i.e., the proposed generalization violates the Nernst heat theorem in the same way as the standard Lifshitz theory with included dc conductivity [compare with Eq. (13)]. In fact, conductivity  $\sigma_0(T) = n|e|\mu$ , where  $\mu$  is a mobility of charge carriers [28]. Although  $\sigma_0(T)$  goes to zero exponentially fast for all dielectrics when  $T$  goes to zero, for most of them this happens due to the vanishing mobility. For instance, the conductivity of  $\text{SiO}_2$  (used in the calculations [24] and, as the plate material, in the experiment [10]) is ionic in nature and is determined by the concentration of impurities (alkali ions) which are always present as trace constituents. According to our result, for this material the generalization of the Lifshitz theory proposed in Ref. [24] violates the Nernst theorem. This is in line with the fact that the extension of the Lifshitz theory with the inclusion of spatial dispersion is controversial and has been debated for long in the literature (see the negative conclusions regarding such an inclusion in Ref. [29] and the recent discussion [30]).

The question of whether there is a possibility to compare the theoretical predictions of Ref. [24] with experimental data should be considered. This could be done with regard to the experiments on measuring the Casimir-Polder interaction between an atom and a  $\text{SiO}_2$  plate [10] and the Casimir interaction between an Au-coated sphere and a Si Plate [15, 16]. In both cases the TE reflection coefficient at zero frequency (which is left undetermined in [24]) does not contribute to the theoretical result. The experiment [10] was successfully used [23] to demonstrate that the inclusion of the dc conductivity of  $\text{SiO}_2$  in the standard Lifshitz theory is inconsistent with the data. The experiments [15, 16] show that the data for the low- and high-conductivity Si plates are consistent with theoretical models which neglect the conductivity or include it, respectively. Unfortunately, all these experiments are not of sufficient precision to discriminate between the predictions of the Lifshitz theory and its generalization [24].

Recently one more experiment has been performed on measuring the difference of the

Casimir forces between an Au sphere and B doped p-type Si plate illuminated with laser pulses [17]. In the absence of laser pulse the concentration of charge carriers in a Si plate was  $\tilde{n} = 5 \times 10^{14} \text{ cm}^{-3}$  and in the presence of pulse  $n_1 = 2.1 \times 10^{19} \text{ cm}^{-3}$  or  $n_2 = 1.4 \times 10^{19} \text{ cm}^{-3}$  for two different absorbed powers  $P_{w1} = 9.3 \text{ mW}$  and  $P_{w2} = 4.7 \text{ mW}$ . The directly measured quantity was  $\Delta F(a) = F^L(a) - F(a)$  where  $F^L$  and  $F$  are the Casimir forces in the presence and in the absence of laser light on the plate, respectively. The experimental data were compared with the Lifshitz theory with neglected or included dc conductivity of the high-resistivity Si in the dark phase. In the latter case the theoretical model was found to be inconsistent with the data. Here, we compare the measurement data of this experiment (shown as crosses in Fig. 1 with experimental errors in force measurement determined at 70% confidence level) with computations on the basis of the standard Lifshitz theory with the dc conductivity neglected in the dark phase (solid lines) and on the basis of Ref. [24] (dashed lines). Figs. 1(a) and 1(b) are related to the absorbed powers  $P_{w1}$ ,  $P_{w2}$ , respectively. The experiment was performed in a high vacuum at  $T = 300 \text{ K}$  (see Ref. [17] for details). The solid lines were computed using the Lifshitz formula for the Casimir force with Si in the dark phase described as dielectric, i.e., by  $\varepsilon(i\xi_l)$  with  $\varepsilon(0) = \varepsilon_0 < \infty$ . In the presence of light the dielectric permittivity

$$\varepsilon^L(i\xi_l) = \varepsilon(i\xi_l) + \frac{\omega_{p(e)}^2}{\xi_l^2} + \frac{\omega_{p(p)}^2}{\xi_l^2} \quad (18)$$

has been used with the values of plasma frequencies for electrons and holes determined in [17] for different absorbed powers. Almost the same results are obtained if the Drude description of charge carriers is used in the presence of light. The dashed lines are obtained using Eq. (14) for the zero frequency TM reflection coefficient with different concentrations of charge carriers  $n = \tilde{n}$  in the dark phase and  $n = 2n_1$  or  $2n_2$  in the presence of light. At all nonzero Matsubara frequencies, in accordance with [24], the standard terms of the Lifshitz formula were used with

$$\tilde{\varepsilon}(i\xi_l) = \varepsilon(i\xi_l) + \frac{\omega_{p(e)}^2}{\xi_l[\xi_l + \gamma^{(e)}]} + \frac{\omega_{p(p)}^2}{\xi_l[\xi_l + \gamma^{(p)}]} \quad (19)$$

(see [17] for the values of all parameters at different absorbed powers). The gold coated sphere was described by the commonly used dielectric permittivity along the imaginary frequency axis (see, e.g., [14, 17, 18]). We have verified that for Au the use of expression (14) instead of the standard zero-frequency term, as given by the Lifshitz theory, leads to numerically the same results up to five significant figures.

As is seen in Fig. 1(a,b), the experimental data are consistent with the theoretical results computed on the basis of the standard Lifshitz theory with the dc conductivity of dielectric Si neglected in the dark phase (the solid lines). The theoretical results computed on the basis of the generalized Lifshitz theory [24] with the modified TM reflection coefficient at zero frequency are excluded by data at a 70% confidence level. The same conclusion follows from the third data set obtained in Ref. [17] at  $P_{w3} = 8.5$  mW absorbed power.

To conclude, we have found the low-temperature behavior of the Casimir-Polder free energy and entropy in atom-plate configuration on the basis of the Lifshitz theory. For a dielectric plate with the dc conductivity of the plate material neglected, the Lifshitz theory was shown to be thermodynamically consistent. With the dc conductivity included, the standard Lifshitz theory of atom-plate interaction violates the Nernst heat theorem. The thermodynamic test was also applied to the recent generalization of the Lifshitz theory taking into account the spatial dispersion due to Debye screening. The proposed generalization is shown to be in violation of Nernst's theorem for a wide range of dielectric materials including doped semiconductors with doping concentration below critical and ionic conductors. This generalization is also inconsistent with the measurements of the difference Casimir force between a metal sphere and Si plate illuminated with laser pulses. The cause for its failure is that  $n$  is not a physically appropriate parameter to characterize the conductivity of material. For example, the same value of  $n$  may characterize two doped semiconductors, one of which is a dielectric (i.e., zero conductivity at  $T = 0$ ) while the other might be metallic (i.e., nonzero conductivity at  $T = 0$ ). The physical reason of why the Lifshitz theory does not allow the inclusion of real conductivity processes calls for further investigation.

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## Figures

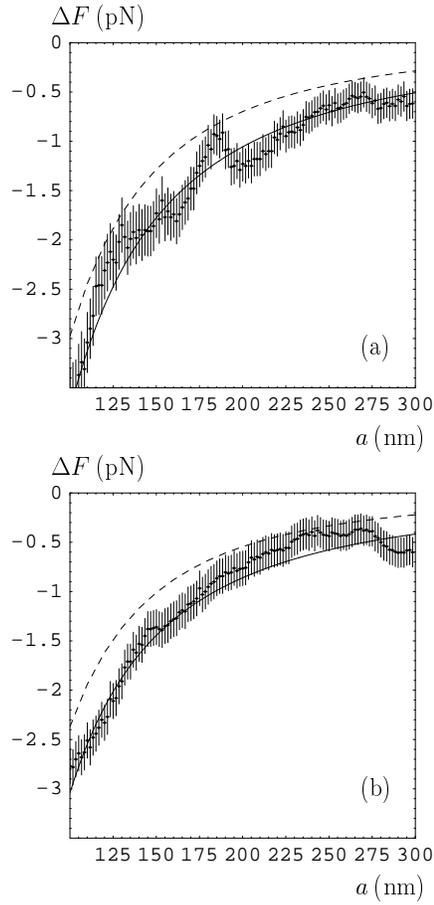


FIG. 1: Difference of the Casimir forces between an Au-coated sphere and a Si plate in the presence and in the absence of laser light on the plate versus separation (a) for the absorbed power of 9.3 mW and (b) 4.7 mW. The experimental data are shown as crosses. Solid and dashed lines indicate the theoretical results calculated using the standard Lifshitz theory with the dc conductivity of Si in the dark phase neglected and the generalization of this theory [24], respectively.